

PLASTIC MEDIUM-POWER

COPLEMENTARY SILICON TRANSISTORS

...designed for general-purpose amplifier and low speed switching applications FEATURES:

* Collector-Emitter Sustaining Voltage-V_{CEO(SUS)} = 60 V (Min) - TIP120,TIP125 = 80 V (Min) - TIP121,TIP126 = 100 V (Min) - TIP122,TIP127

* Collector-Emitter Saturation Voltage

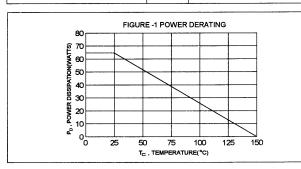
 $\rm V_{\rm CE(set)}=2.0~V$ (Max.) @ $\rm I_{\rm C}=3.0~A$ * Monolithic Construction with Built-in Base-Emitter Shunt Resistor

MAXIMUM RATINGS

Characteristic	Symbol	TIP120 TIP125	TIP121 TIP126	TIP122 TIP127	Unit
Collector-Emitter Voltage	V _{CEO}	60	80	100	٧
COllector-Base Voltage	V _{CBO}	60	80	100	٧
Emitter-Base Voltage	V _{EBO}	5.0			٧
Collector Current-Continuous -Peak	I _C	5.0 8.0		A	
Base Current	l _B	120			mA
Total Power Dissipation @T _c = 25°C Derate above 25°C	P _D	65 0.52			w/°c
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	- 65 to +150			°C

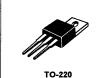
THERMAL CHARACTERISTICS

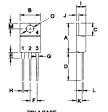
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	R⊕jc	1.92	°C/W



NPN	PNP
TIP120	TIP125
TIP121	TIP126
TIP122	TIP127

5.0 AMPERE DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS 60-100 VOLTS 65 WATTS





1.BASE 2.COLLECTOR 3.EMITTER 4.COLLECTOR(CASE)

DIM	MILLIMETERS				
DIM	MIN	MAX			
Α	14.68	15.31			
В	9.78	10.42			
С	5.01	6.52			
D	13.06	14.62			
Ε	3.57	4.07			
F	2.42	3.66			
G	1.12	1.36			
н	0.72	0.96			
1	4.22	4.98			
J	1.14	1.38			
K	2.20	2.97			
L	0.33	0.55			
М	2.48	2.98			
0	3.70	3.90			

TIP120, TIP121, TIP122 NPN / TIP125, TIP126, TIP127 PNP

ELECTRICAL CHARACTERISTICS (T_c = 25°C unless otherwise noted)

	Characteristic	Symbol	Min	Max	Unit
--	----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (1)		V _{CEO(sus)}	V		V
(I _C = 30 mA, I _B = 0)	TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	- CEO(sus)	60 80 100		
Collector Cutoff Current (V _{CE} = 30 V, I _B = 0) (V _{CE} = 40 V, I _B = 0) (V _{CE} = 50 V, I _B = 0)	TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	I _{CEO}		0.5 0.5 0.5	mA
Collector Cutoff Current ($V_{CB} = 60 \text{ V}, I_{E} = 0 \text{)}$ ($V_{CB} = 80 \text{ V}, I_{E} = 0 \text{)}$ ($V_{CB} = 100 \text{ V}, I_{E} = 0 \text{)}$	TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	Ісво		0.2 0.2 0.2	mA
Emitter Cutoff Current (V _{EB} = 5.0 V,I _C = 0)		I _{EBO}		2.0	mA

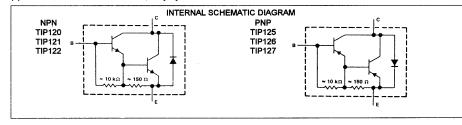
ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 0.5 \text{ A, } V_{CE} = 3.0 \text{ V}$) ($I_C = 3.0 \text{ A, } V_{CE} = 3.0 \text{ V}$)	hFE	1000 1000		
Collector-Emitter Saturation Voltage ($I_C = 3.0 \text{ A}$, $I_B = 12 \text{ mA}$) ($I_C = 5.0 \text{ A}$, $I_B = 20 \text{ mA}$)	V _{CE(sat)}		2.0 4.0	v
Base-Emitter On Voltage (I _C = 3.0 A, V _{CE} = 3.0 V)	V _{BE(on)}		2.5	V

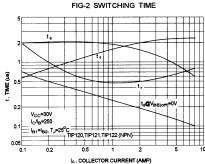
DYNAMIC CHARACTERISTICS

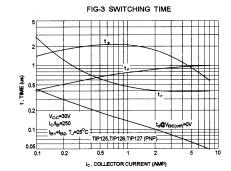
Small-Signal Current Gain (I _C = 3.0 A,V _{CE} = 4.0 V, f = 1.0 MHz.)	h _{fe}	4.0		
Output Capacitance (V _{CB} = 10 V, I _E = 0 , f = 0.1 MHz) TIP120,TIP121,TIP122 TIP125,TIP126,TIP127	Сов		300 250	pF

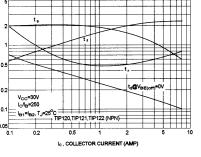
(1) Pulse Test: Pulse width = 300 us , Duty Cycle ≤ 2.0%

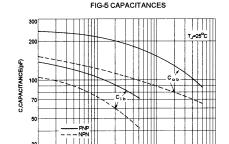


TIP120, TIP121, TIP122 NPN / TIP125, TIP126, TIP127 PNP









2

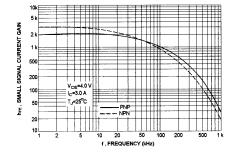
V_R, REVERSE VOLTAGE (VOLTS)

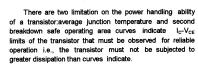
5 10

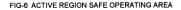
0.1 0.2

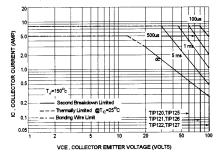
0.5











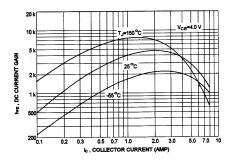
The data of FIG-6 is base on T_{J(PK)}=150 °C;T_C is variable depending on power level second breakdown pulse limits are valid for duty cycles to 10% provided T_{J(PK)} ≤150°C ,At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limi tations imposed by second breakdown.

TIP120, TIP121, TIP122 NPN / TIP125, TIP126 TIP127 PNP

PNP TIP125,TIP126,TIP127



FIG-7 DC CURRENT GAIN



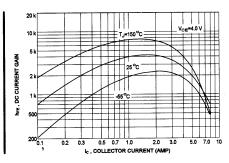
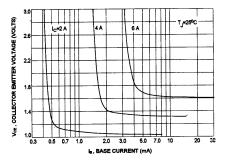


FIG-8 COLLECTOR SATURATION REGION



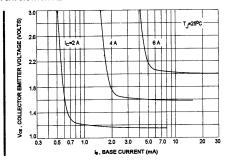


FIG-9 "ON" VOLTAGES

